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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit
Speed	240MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, MMC/SD, QSPI, SCI, SPI, SSI, UART/USART, USB
Peripherals	DMA, LCD, LVD, POR, PWM, WDT
Number of I/O	70
Program Memory Size	3MB (3M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	640K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 3.6V
Data Converters	A/D 16x12b SAR; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LFQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r7fs7g27g3a01cfp-aa0

R7FS7G2xxxA01CLK

	A	B	C	D	E	F	G	H	J	K	L	M	N	
13	P407	P409	P412	P708	P711	VCC	P212 /EXTAL	XCIN	VCL0	P702	P405	P402	P400	13
12	USB_DM	USB_DP	P410	P414	P710	VSS	P213 /XTAL	XCOUT	VBATT	P701	P404	P511	VCC	12
11	VCC_ USB	VSS_ USB	P207	P411	P415	P712	P705	P704	P703	P403	P401	P512	VSS	11
10	P205	P206	P204	P408	P413	P709	P713	P700	P406	P003	P000	P002	P001	10
9	P203	P313	P202	VSS						P004	P006	P009	P008	9
8	VCL1	VSS	P200	VCC						P005	AVSS0	VREFL0	VREFH0	8
7	VLO	VLO	RES	P310						P007	AVCC0	VREFL	VREFH	7
6	VCC_ DCDC	P201/MD	P312	P305						P505	P506	P015	P014	6
5	P309	P311	P308	P303	NC					P503	P504	VSS	VCC	5
4	P307	P306	P304	P109/TDO	P114	P608	P604	P600	P105	P500	P502	P501	VCL2	4
3	VSS	VCC	P301	P112	P115	P610	P614	P603	P107	P106	P104	VSS	VCC	3
2	P302	P300/TCK /SWCLK	P111	VCC	P609	P612	VSS	P605	P601	VCC	P800	P101	P801	2
1	P108/TMS /SWDIO	P110/TDI	P113	VSS	P611	P613	VCC	VCL_F	P602	VSS	P103	P102	P100	1
	A	B	C	D	E	F	G	H	J	K	L	M	N	

Figure 1.6 Pin assignment for 145-pin LGA (top view)

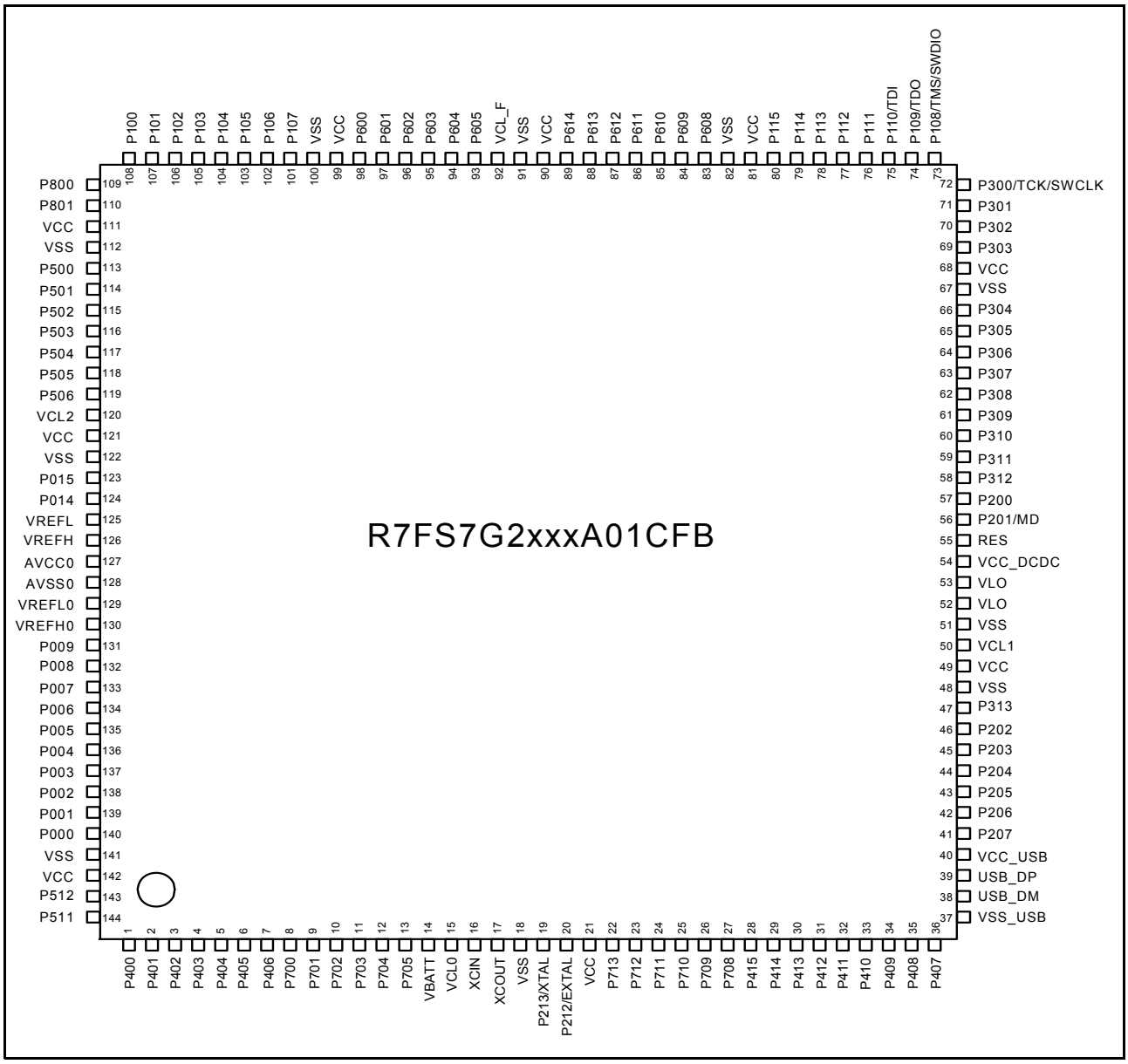


Figure 1.7 Pin assignment for 144-pin LQFP (top view)

1.7 Pin Lists

Table 1.17 Pin list (1/12)

Pin number						Power, System, Clock, Debug,	I/O port	Extbus		Timers				Communication interfaces									Analog		HMI		
BGA224	BGA176	LQFP176	LGA145	LQFP144	LQFP100			External bus	SDRAM	AGT	GPT	GPT	RTC	USBFS, CAN	SCI0,2,4,6,8 (30 MHz)	SCI1,3,5,7,9 (30 MHz)	IIC	SPI, QSPI	SSI	MII (25 MHz)	RMII (50 MHz)	USBHS	SDHI	ADC12	DAC12, ACMPHS	CTSU	Interrupt	GLCDC, PDC
N13	N13	1	N13	1	1	-	P400	-	-	-	-	GTIOC6A_A	-	-	SCK4_B	SCK7_A	SCL0_A	-	AUDIO_CLK	ET1_TX_CLK	-	-	-	ADTRG1_B	-	-	IRQ0	-
P15	R15	2	L11	2	2	-	P401	-	-	-	GETRGA_B	GTIOC6B_A	-	CTX0_B	CTS4_RTS4_B/SS4_B	TXD7_A/MOSI7_A/SDA7_A	SDA0_A	-	-	ET0_MDC	ET0_MDC	-	-	-	-	-	IRQ5-DS	-
N14	P14	3	M13	3	3	-	P402	-	-	AGTIO0_B/AGTIO1_B	-	-	RTCIC0	CRX0_B	-	RXD7_A/MISO7_A/SCL7_A	-	-	-	ET0_MDIO	ET0_MDIO	-	-	-	-	-	IRQ4-DS	-
N15	M12	4	K11	4	4	-	P403	-	-	AGTIO0_C/AGTIO1_C	-	GTIOC3A_B	RTCIC1	-	-	CTS7_RTS7_A/SS7_A	-	-	SSISCK0_A	ET1_MDC	ET1_MDC	-	-	-	-	-	-	PIXD7
K10	M13	5	L12	5	5	-	P404	-	-	-	-	GTIOC3B_B	RTCIC2	-	-	-	-	-	SSIWS0_A	ET1_MDIO	ET1_MDIO	-	-	-	-	-	-	PIXD6
M13	P15	6	L13	6	6	-	P405	-	-	-	-	GTIOC1A_B	-	-	-	-	-	-	SSITXD0_A	ET1_TX_EN	RMII1_TXD_EN	-	-	-	-	-	-	PIXD5
J9	N14	7	J10	7	7	-	P406	-	-	-	-	GTIOC1B_B	-	-	-	-	-	-	SSIRXD0_A	ET1_RX_ER	RMII1_TXD1	-	-	-	-	-	-	PIXD4
M14	N15	8	H10	8	-	-	P700	-	-	-	-	GTIOC5A_B	-	-	-	-	-	-	-	ET1_ETXD1	RMII1_TXD0	-	-	-	-	-	-	PIXD3
M15	M14	9	K12	9	-	-	P701	-	-	-	-	GTIOC5B_B	-	-	-	-	-	-	-	ET1_ETXD0	REF50CK1	-	-	-	-	-	-	PIXD2
K11	L12	10	K13	10	-	-	P702	-	-	-	-	GTIOC6A_B	-	-	-	-	-	-	-	ET1_ERXD1	RMII1_RXD0	-	-	-	-	-	-	PIXD1
J8	M15	11	J11	11	-	-	P703	-	-	-	-	GTIOC6B_B	-	-	-	-	-	-	-	ET1_ERXD0	RMII1_RXD1	-	-	-	-	-	-	PIXD0
J10	L13	12	H11	12	-	-	P704	-	-	-	-	-	-	-	-	-	-	-	-	ET1_RX_CLK	RMII1_RX_ER	-	-	-	-	-	-	HSYNC
L13	K12	13	G11	13	-	-	P705	-	-	-	-	-	-	-	-	-	-	-	-	ET1_CRS	RMII1_CRS_DV	-	-	-	-	-	-	PIXCLK
L14	L14	14	-	-	-	-	P706	-	-	-	-	-	-	-	-	RXD3_B/MISO3_B/SCL3_B	-	-	-	-	-	USBHS_OVRCURB	-	-	-	-	IRQ7	-
L15	L15	15	-	-	-	-	P707	-	-	-	-	-	-	-	-	TXD3_B/MOSI3_B/SDA3_B	-	-	-	-	-	USBHS_OVRCURA	-	-	-	-	IRQ8	-

Derating is the systematic reduction of load for improved reliability.

Table 2.2 Recommended operating conditions

Item	Symbol	Value	Min	Typ	Max	Unit
Power supply voltages	VCC	When USB/SDRAM is not used	2.7	-	3.6	V
		When USB/SDRAM is used	3.0	-	3.6	V
	VSS		-	0	-	V
USB power supply voltages	VCC_USB, VCC_USBHS		-	VCC	-	V
	VSS_USB, AVSS_USBHS, PVSS_USBHS, VSS1_USBHS, VSS2_USBHS		-	0	-	V
Switching regulator power supply voltage	VCC_DCDC	When switching regulator is used	-	VCC	-	V
		When switching regulator is not used	-	0	-	V
VBATT power supply voltage	VBATT		2.0		3.6	V
Analog power supply voltages	AVCC0		-	VCC	-	V
	AVSS0		-	0	-	V

2.2 DC Characteristics

2.2.1 Tj/Ta Definition

Table 2.3 DC characteristics
Conditions: Products with operating temperature (T_a) –40 to +105°C

Item	Symbol	Typ	Max	Unit	Test conditions
Permissible junction temperature	Tj	-	125	°C	High-speed mode Low-speed mode Subosc-speed mode

Note: Make sure that Tj = T_a + θja × total power consumption (W), where total power consumption = (VCC – V_{OH}) × ΣI_{OH} + V_{OL} × ΣI_{OL} + I_{CC}max × VCC.

2.2.2 I/O V_{IH}, V_{IL}

Table 2.4 I/O V_{IH}, V_{IL} (1/2)

Item			Symbol	Min	Typ	Max	Unit
Input voltage (except for Schmitt trigger input pins)	Peripheral function pin	EXTAL(external clock input), WAIT, SPI	V_{IH}	VCC × 0.8	-	VCC + 0.3	V
			V_{IL}	–0.3	-	VCC × 0.2	
		D00 to D15, DQ00 to DQ15	V_{IH}	VCC × 0.7	-	VCC + 0.3	
			V_{IL}	–0.3	-	VCC × 0.3	
		ETHERC	V_{IH}	2.3	-	VCC + 0.3	
			V_{IL}	–0.3	-	VCC × 0.2	
		IIC (SMBus)*1	V_{IH}	2.1	-	VCC + 0.3	
			V_{IL}	–0.3	-	0.8	
		IIC (SMBus)*2	V_{IH}	2.1	-	5.8	
			V_{IL}	–0.3	-	0.8	

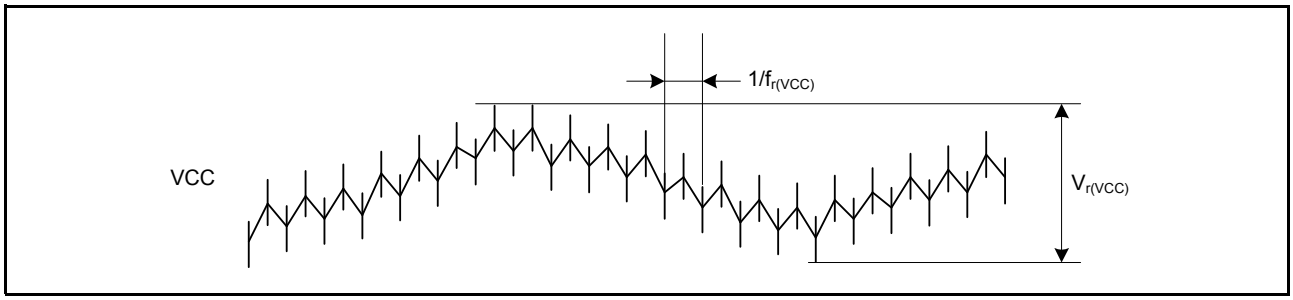


Figure 2.2 Ripple waveform

2.3 AC Characteristics

2.3.1 Frequency

Table 2.10 Operation frequency value in high-speed mode

Item			Symbol	Min	Typ	Max	Unit
Operation frequency	System clock (ICLK*2)		f	-	-	240	MHz
	Peripheral module clock (PCLKA)*2			-	-	120	
	Peripheral module clock (PCLKB)*2			-	-	60	
	Peripheral module clock (PCLKC)*2			-*3	-	60	
	Peripheral module clock (PCLKD)*2			-	-	120	
	Flash interface clock (FCLK)*2			-*1	-	60	
	External bus clock (BCLK)*2			-	-	120	
	EBCLK pin output			-	-	60	
	SDCLK pin output	VCC ≥ 3.0 V		-	-	120	

Note 1. FCLK must run at a frequency of at least 4 MHz when programming or erasing the flash memory.
Note 2. See section 9, Clock Generation Circuit in User's Manual for the relationship between the ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK, and BCLK frequencies.
Note 3. When the ADC12 is used, the PCLKC frequency must be at least 1 MHz.

Table 2.11 Operation frequency value in low-speed mode

Item		Symbol	Min	Typ	Max	Unit
Operation frequency	System clock (ICLK)*2	f	-	-	1	MHz
	Peripheral module clock (PCLKA)*2		-	-	1	
	Peripheral module clock (PCLKB)*2		-	-	1	
	Peripheral module clock (PCLKC)*2,*3		-*3	-	1	
	Peripheral module clock (PCLKD)*2		-	-	1	
	Flash interface clock (FCLK)*1, *2		-	-	1	
	External bus clock (BCLK)		-	-	1	
	EBCLK pin output		-	-	1	

Note 1. Programming or erasing the flash memory is disabled in low-speed mode.
Note 2. See section 9, Clock Generation Circuit in User's Manual for the relationship between the ICLK, PCLKA, PCLKB, PCLKC, PCLKD, FCLK, and BCLK frequencies.
Note 3. When the ADC12 is used, the PCLKC frequency must be set to at least 1 MHz.

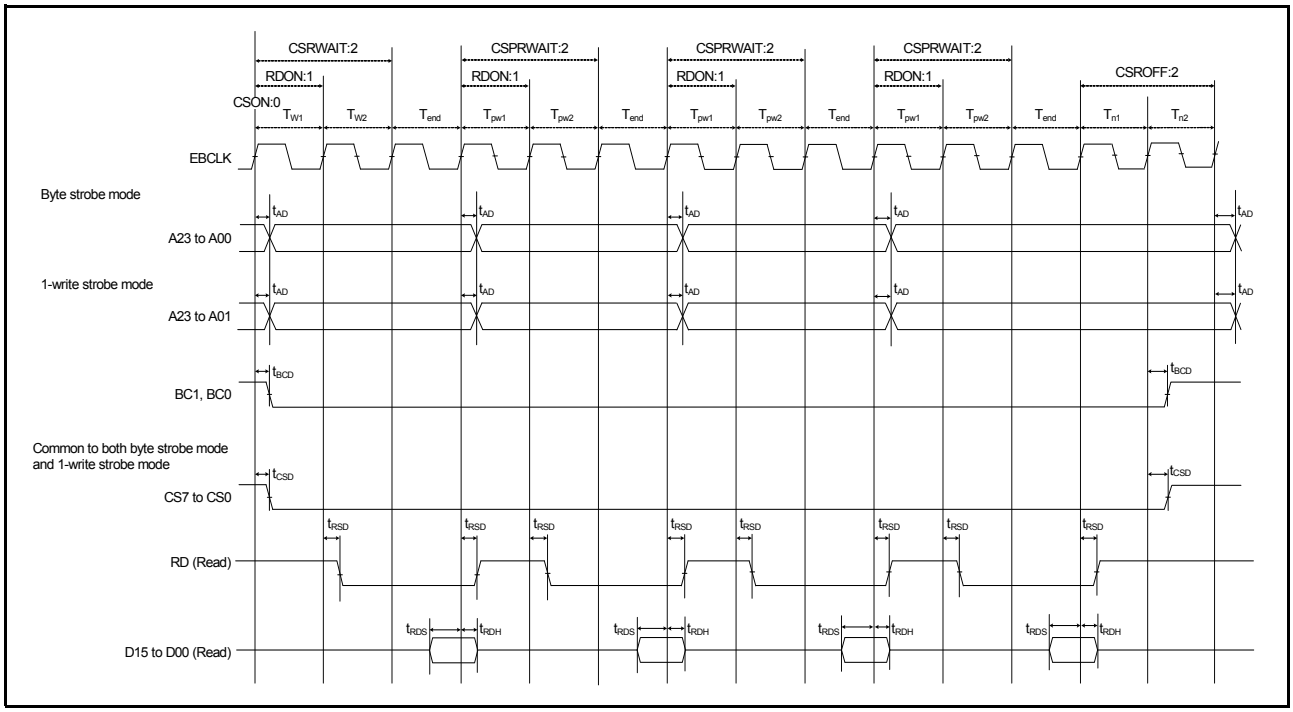
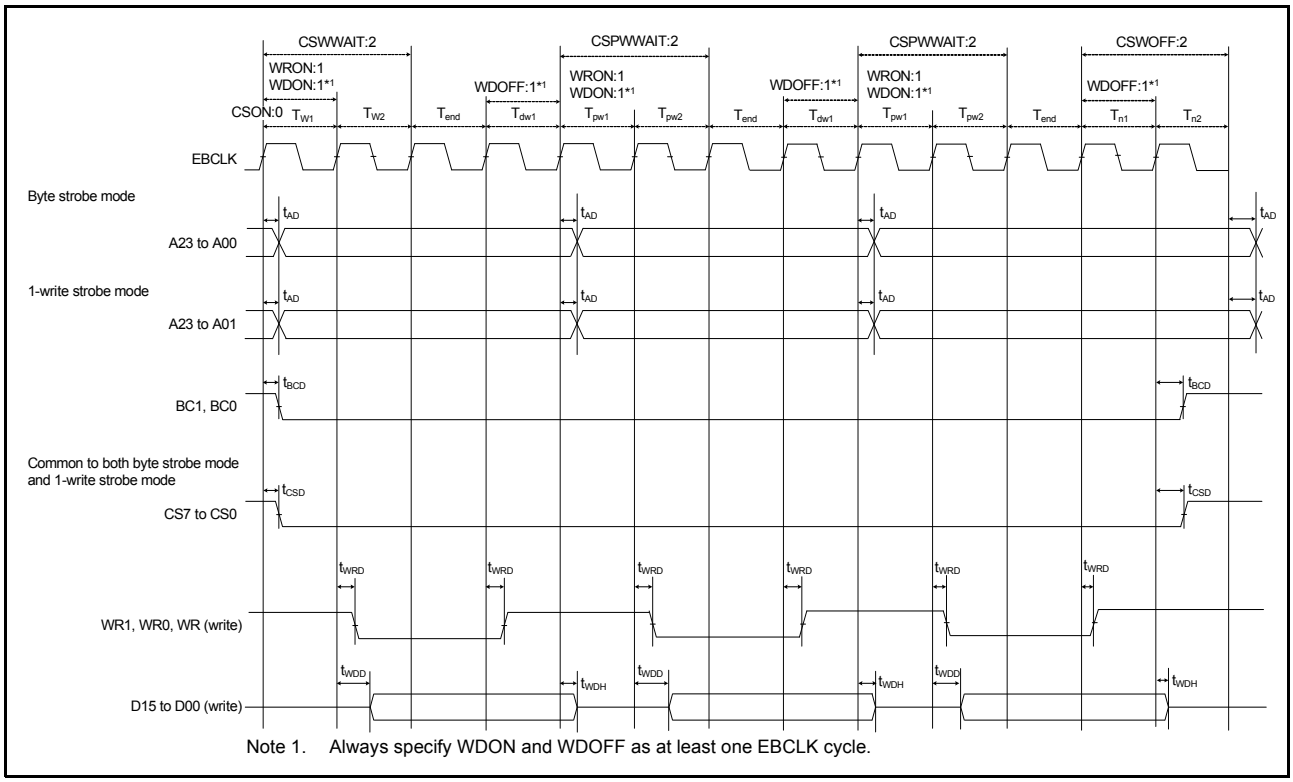
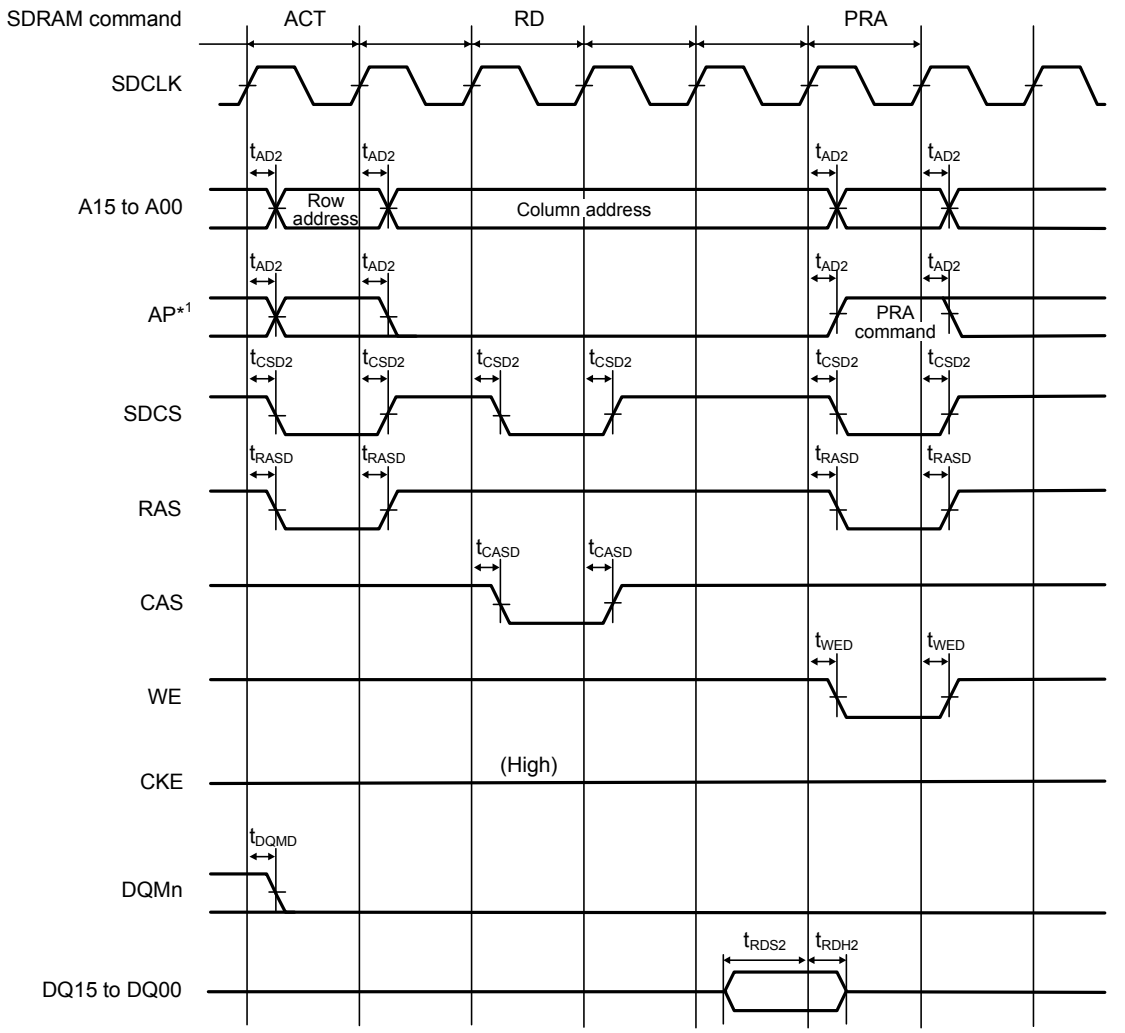


Figure 2.16 External bus timing for page read cycle with bus clock synchronized



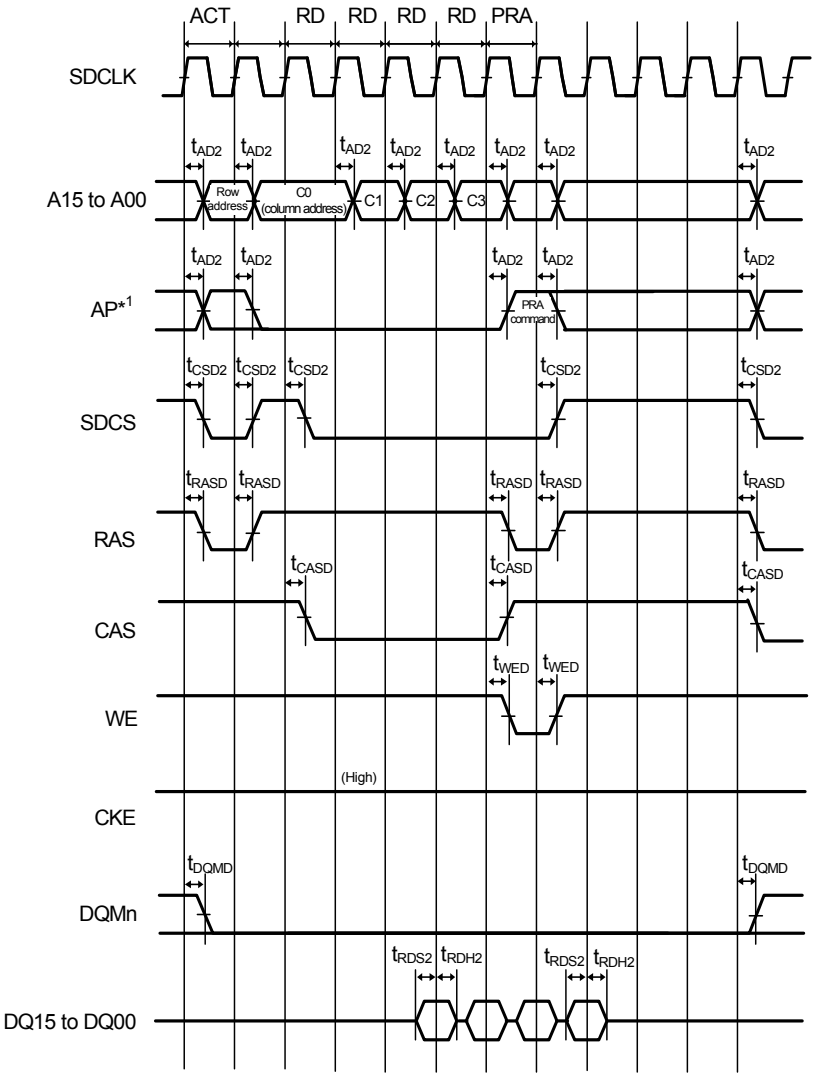
Note 1. Always specify WDON and WDOFF as at least one EBCLK cycle.

Figure 2.17 External bus timing for page write cycle with bus clock synchronized



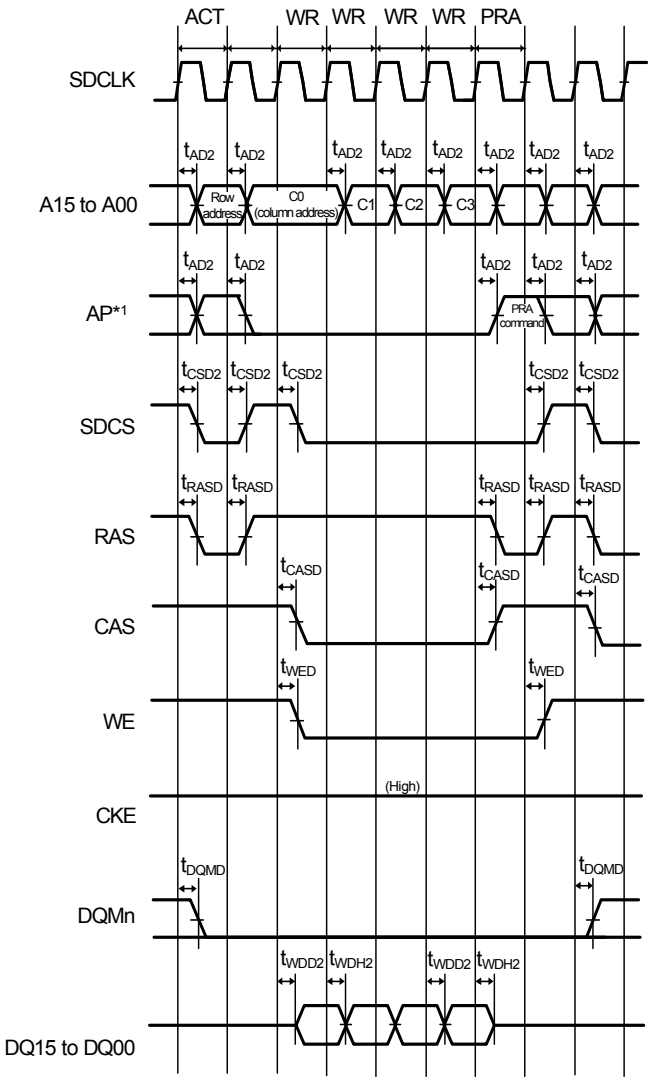
Note 1. Address pins are for output of the precharge-select command (Precharge-sel) for the SDRAM.

Figure 2.19 SDRAM single read timing



Note 1. Address pins are for output of the precharge-select command (Precharge-sel) for the SDRAM.

Figure 2.21 SDRAM multiple read timing



Note 1. Address pins are for output of the precharge-select command (Precharge-sel) for the SDRAM.

Figure 2.22 SDRAM multiple write timing

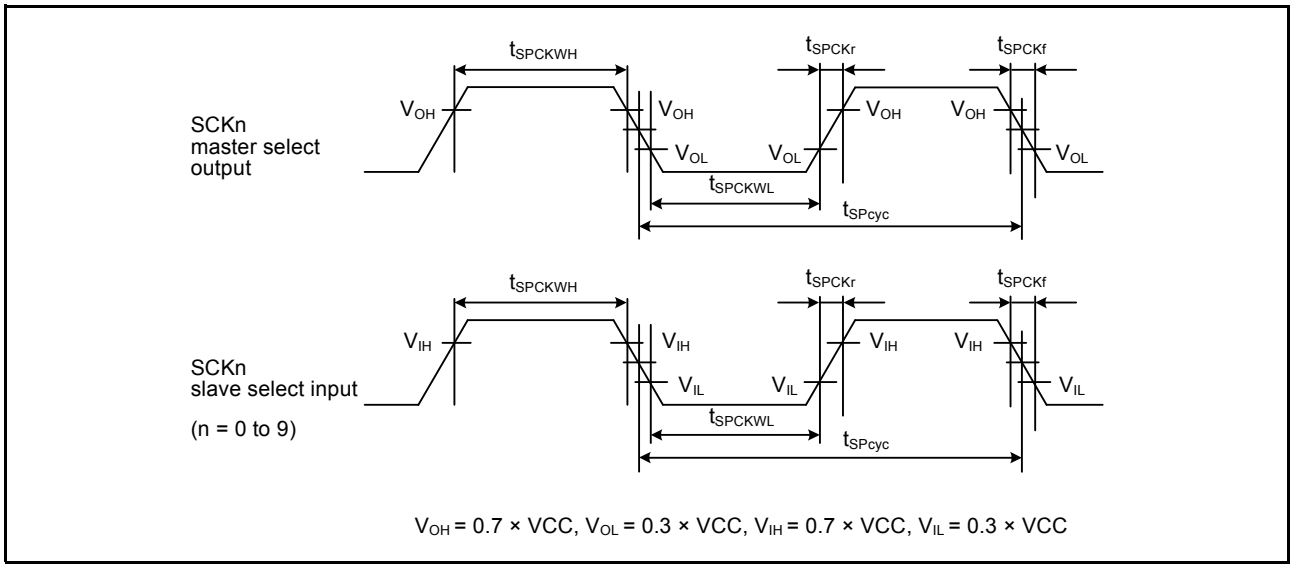


Figure 2.37 SCI simple SPI mode clock timing

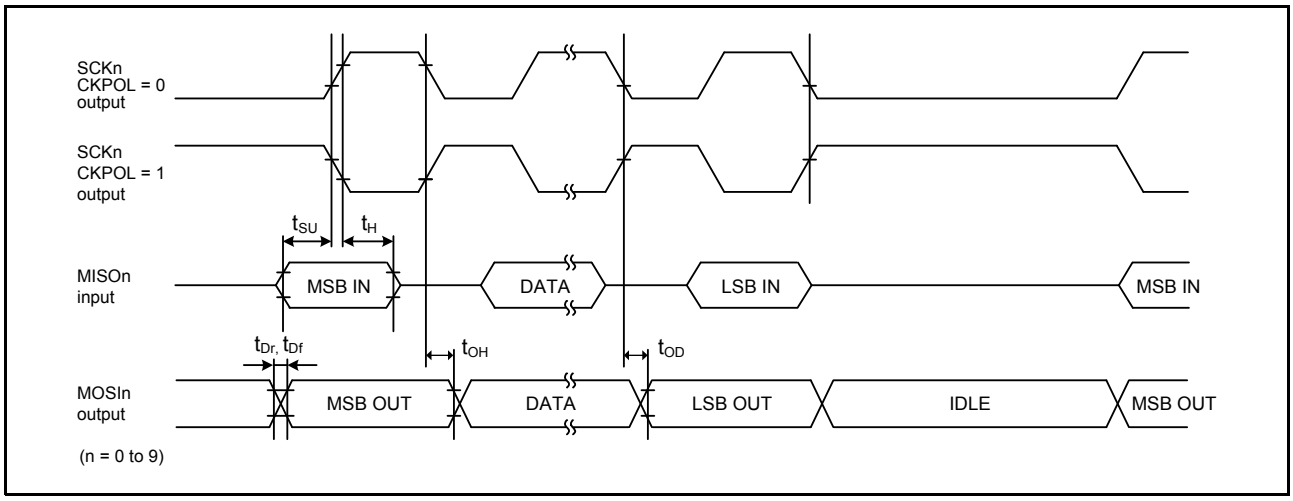


Figure 2.38 SCI simple SPI mode timing for master when CKPH = 1

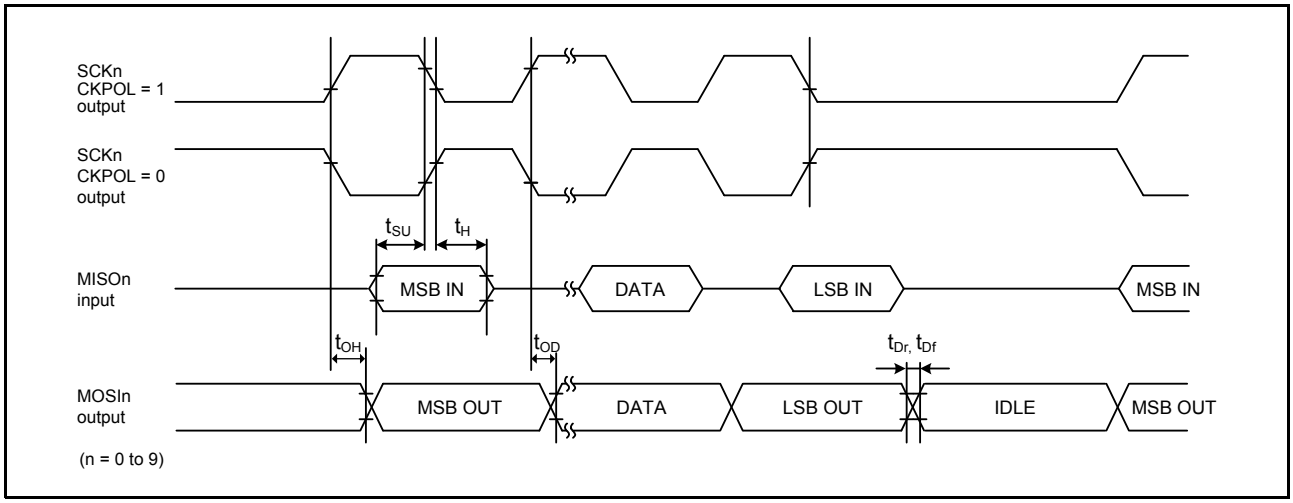


Figure 2.39 SCI simple SPI mode timing for master when CKPH = 0

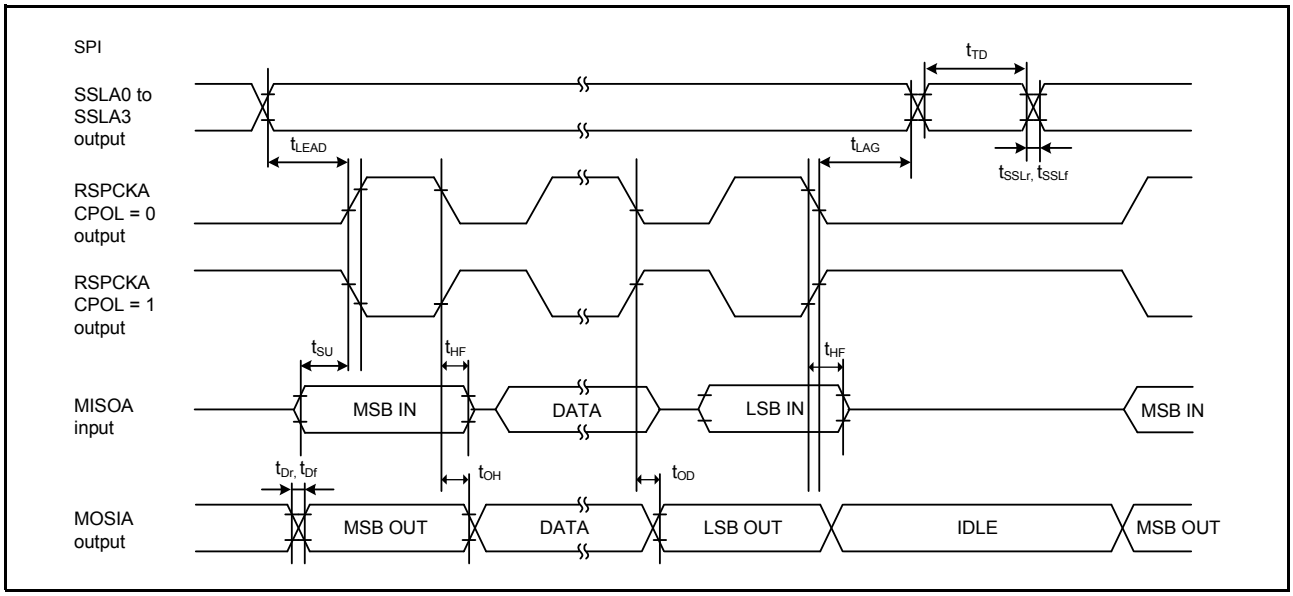


Figure 2.45 SPI timing for master when CPHA = 0 and the bit rate is set to PCLKA/2

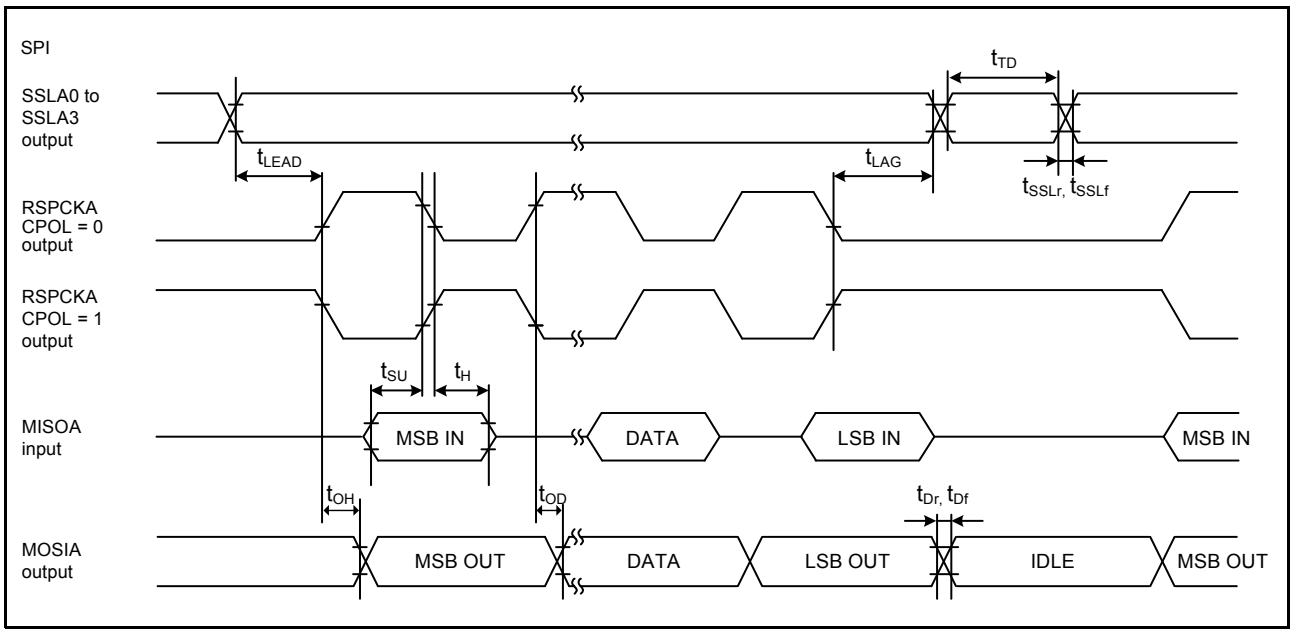


Figure 2.46 SPI timing for master when CPHA = 1 and the bit rate is set to PCLKA/2

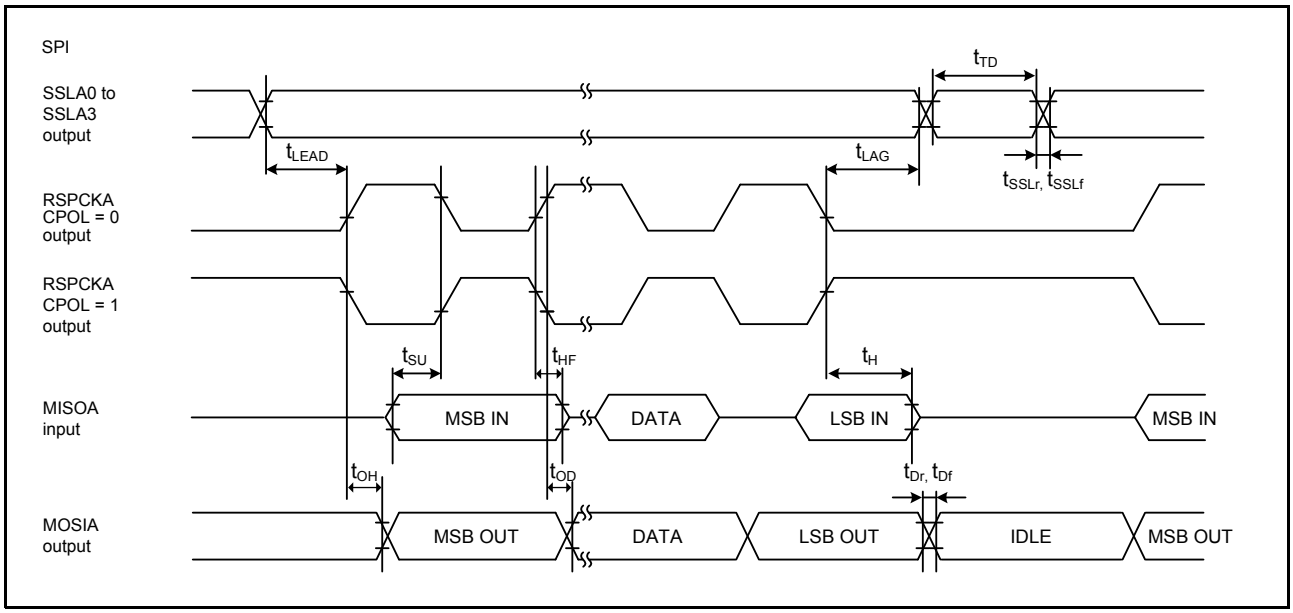


Figure 2.47 SPI timing for master when CPHA = 1 and the bit rate is set to PCLKA/2

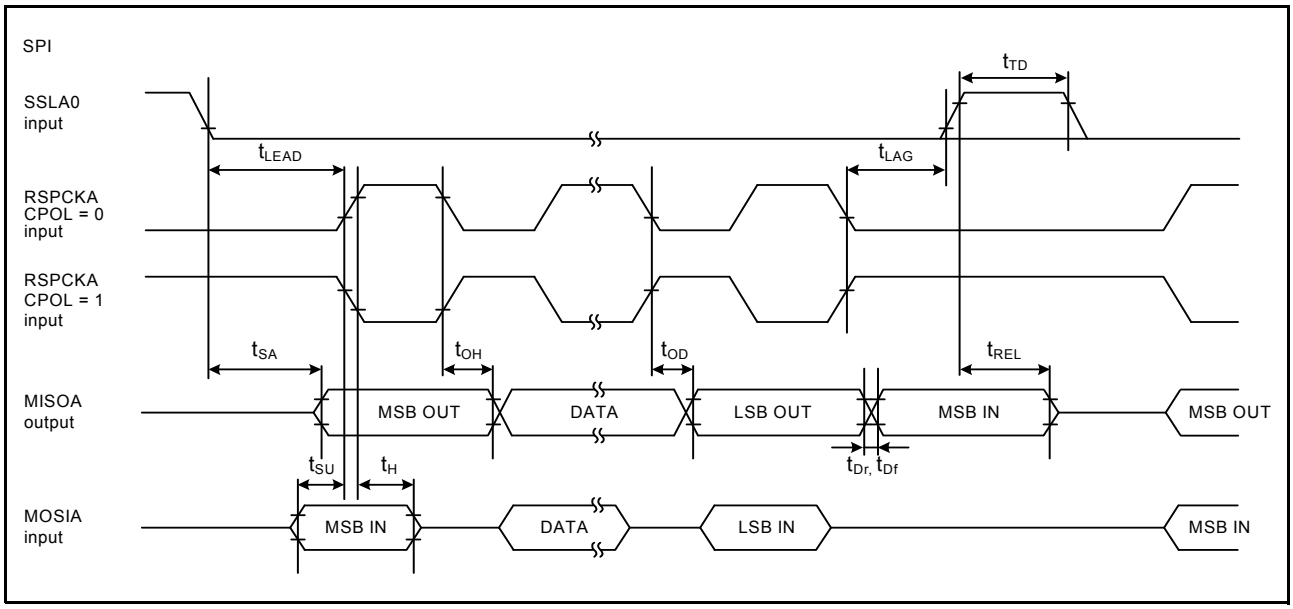


Figure 2.48 SPI timing for slave when CPHA = 0

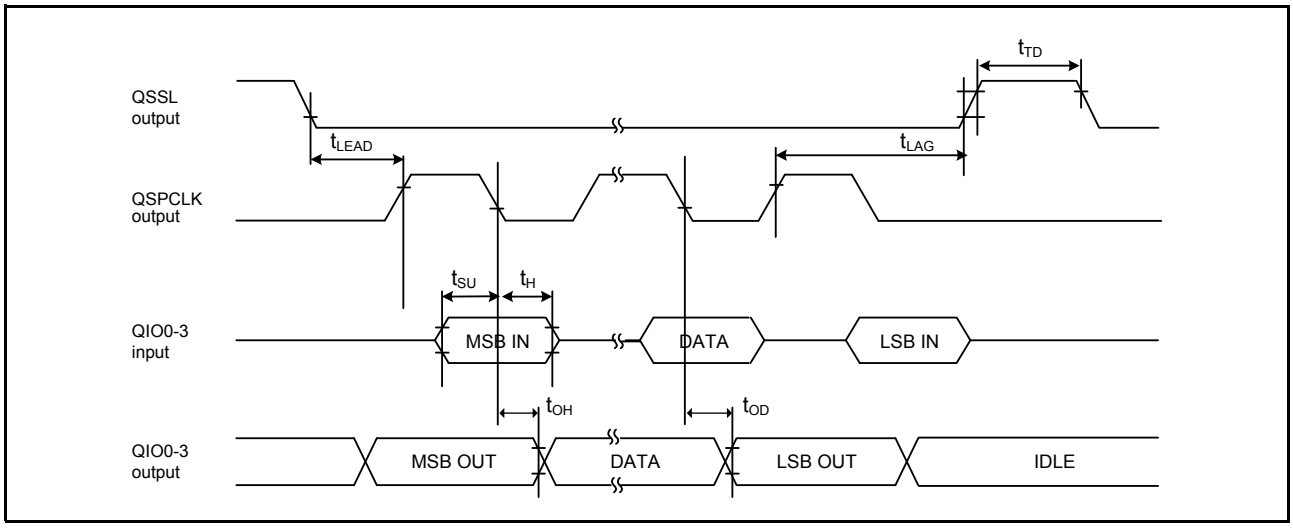


Figure 2.51 Transmit and receive timing

2.3.13 IIC Timing

Table 2.27 IIC timing (1) (1/2)

Conditions: Middle drive output is selected in the port drive capability bit in the PmnPFS register for the following pins: SDA0_B, SCL0_B, SDA1_A, SCL1_A, SDA1_B, SCL1_B.
The following pins do not require setting: SCL0_A, SDA0_A, SCL2, SDA2.

Item		Symbol	Min*1, *2	Max	Unit	Test conditions
IIC (Standard mode, SMBus) ICFER.FMPE = 0	SCL input cycle time	t_{SCL}	6 (12) × t_{IICcyc} + 1300	-	ns	Figure 2.52
	SCL input high pulse width	t_{SCLH}	3 (6) × t_{IICcyc} + 300	-	ns	
	SCL input low pulse width	t_{SCLL}	3 (6) × t_{IICcyc} + 300	-	ns	
	SCL, SDA input rise time	t_{Sr}	-	1000	ns	
	SCL, SDA input fall time	t_{Sf}	-	300	ns	
	SCL, SDA input spike pulse removal time	t_{SP}	0	1 (4) × t_{IICcyc}	ns	
	SDA input bus free time when wakeup function is disabled	t_{BUF}	3 (6) × t_{IICcyc} + 300	-	ns	
	SDA input bus free time when wakeup function is enabled	t_{BUF}	3 (6) × t_{IICcyc} + 4 × t_{Pcyc} + 300	-	ns	
	START condition input hold time when wakeup function is disabled	t_{STAH}	t_{IICcyc} + 300	-	ns	
	START condition input hold time when wakeup function is enabled	t_{STAH}	1 (5) × t_{IICcyc} + t_{Pcyc} + 300	-	ns	
	Repeated START condition input setup time	t_{STAS}	1000	-	ns	
	STOP condition input setup time	t_{STOS}	1000	-	ns	
	Data input setup time	t_{SDAS}	t_{IICcyc} + 50	-	ns	
	Data input hold time	t_{SDAH}	0	-	ns	
	SCL, SDA capacitive load	C_b	-	400	pF	

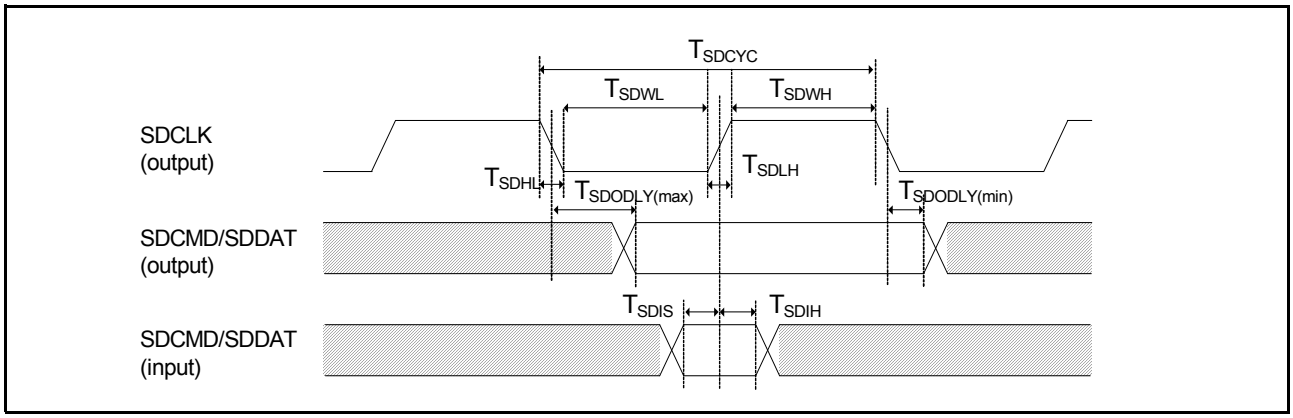


Figure 2.57 SD/MMC Host Interface signal timing

2.3.16 ETHERC Timing

Table 2.31 ETHERC timing

Conditions: ETHERC (RMII): Middle drive output is selected in the port drive capability bit in the PmnPFS register for the following pins: ET0_MDC, ET0_MDIO, ET1_MDC, and ET1_MDIO
For other pins, high drive output is selected in the port drive capability bit in the PmnPFS register.
ETHERC (MII): Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Item		Symbol	Min	Max	Unit	Test conditions
ETHERC (RMII)	REF50CK cycle time	T_{ck}	20	-	ns	Figure 2.58 to Figure 2.61
	REF50CK frequency, typical 50 MHz	-	-	50 + 100 ppm	MHz	
	REF50CK duty	-	35	65	%	
	REF50CK rise/fall time	$T_{ckr/ckf}$	0.5	3.5	ns	
	RMII_xxxx*1 output delay	T_{co}	2.5	12.0	ns	
	RMII_xxxx*2 setup time	T_{su}	3	-	ns	
	RMII_xxxx*2 hold time	T_{hd}	1	-	ns	
	RMII_xxxx*1, *2 rise/fall time	T_r/T_f	0.4	4	ns	
	ET_WOL output delay	t_{WOLd}	1	23.5	ns	Figure 2.62
ETHERC (MII)	ET_TX_CLK cycle time	t_{Tcyc}	40	-	ns	-
	ET_TX_EN output delay	t_{TENd}	1	20	ns	Figure 2.63
	ET_ETXD0 to ET_ETXD3 output delay	t_{MTDd}	1	20	ns	
	ET_CRS setup time	t_{CRSs}	10	-	ns	
	ET_CRS hold time	t_{CRSh}	10	-	ns	
	ET_COL setup time	t_{COLs}	10	-	ns	Figure 2.64
	ET_COL hold time	t_{COLh}	10	-	ns	
	ET_RX_CLK cycle time	t_{TRcyc}	40	-	ns	-
	ET_RX_DV setup time	t_{RDVs}	10	-	ns	Figure 2.65
	ET_RX_DV hold time	t_{RDVh}	10	-	ns	
	ET_ERXD0 to ET_ERXD3 setup time	t_{MRDs}	10	-	ns	
	ET_ERXD0 to ET_ERXD3 hold time	t_{MRDh}	10	-	ns	
	ET_RX_ER setup time	t_{RERs}	10	-	ns	Figure 2.66
	ET_RX_ER hold time	t_{RESh}	10	-	ns	
	ET_WOL output delay	t_{WOLd}	1	23.5	ns	Figure 2.67

Note 1. RMII_TXD_EN, RMII_TXD1, RMII_TXD0.
Note 2. RMII_CRS_DV, RMII_RXD1, RMII_RXD0, RMII_RX_ER.

Table 2.41 A/D conversion characteristics for unit 1 (2/2)
Conditions: PCLKC = 1 to 60 MHz

Item			Min	Typ	Max	Unit	Test conditions
Quantization error			-	±0.5	-	LSB	-
Resolution			-	-	12	Bits	-
Channel-dedicated sample-and-hold circuits in use (AN100 to AN102)	Conversion time*1 (operation at PCLKC = 60 MHz)	Permissible signal source impedance Max. = 1 kΩ	1.06 (0.4 + 0.25)*2	-	-	µs	• Sampling of channel-dedicated sample-and-hold circuits in 24 states • Sampling in 15 states
	Offset error		-	±1.5	±3.5	LSB	AN100 to AN102 = 0.25 V
	Full-scale error		-	±1.5	±3.5	LSB	AN100 to AN102 = VREFH - 0.25 V
	Absolute accuracy		-	±2.5	±5.5	LSB	-
	DNL differential nonlinearity error		-	±1.0	±2.0	LSB	-
	INL integral nonlinearity error		-	±1.5	±3.0	LSB	-
	Holding characteristics of sample-and hold circuits		-	-	20	µs	-
	Dynamic range		0.25	-	VREFH – 0.25	V	-
Channel-dedicated sample-and-hold circuits not in use (AN100 to AN102)	Conversion time*1 (Operation at PCLKC = 60 MHz)	Permissible signal source impedance Max. = 1 kΩ	0.88 (0.667)*2	-	-	µs	Sampling in 40 states
	Offset error		-	±1.0	±2.5	LSB	-
	Full-scale error		-	±1.0	±2.5	LSB	-
	Absolute accuracy		-	±2.0	±4.5	LSB	-
	DNL differential nonlinearity error		-	±0.5	±1.5	LSB	-
	INL integral nonlinearity error		-	±1.0	±2.5	LSB	-
High-precision channels (AN103 to AN106)	Conversion time*1 (Operation at PCLKC = 60 MHz)	Permissible signal source impedance Max. = 1 kΩ	0.48 (0.267)*2	-	-	µs	Sampling in 16 states
		Max. = 300Ω	0.40 (0.183)*2	-	-	µs	Sampling in 11 states VCC = AVCC0 = 3.0 to 3.6 V 3.0 V ≤ VREFH ≤ AVCC0
	Offset error		-	±1.0	±2.5	LSB	-
	Full-scale error		-	±1.0	±2.5	LSB	-
	Absolute accuracy		-	±2.0	±4.5	LSB	-
	DNL differential nonlinearity error		-	±0.5	±1.5	LSB	-
	INL integral nonlinearity error		-	±1.0	±2.5	LSB	-
Normal-precision channels (AN116 to AN120)	Conversion time*1 (Operation at PCLKC = 60 MHz)	Permissible signal source impedance Max. = 1 kΩ	0.88 (0.667)*2	-	-	µs	Sampling in 40 states
	Offset error		-	±1.0	±5.5	LSB	-
	Full-scale error		-	±1.0	±5.5	LSB	-
	Absolute accuracy		-	±2.0	±7.5	LSB	-
	DNL differential nonlinearity error		-	±0.5	±4.5	LSB	-
	INL integral nonlinearity error		-	±1.0	±5.5	LSB	-

Note: These specification values apply when there is no access to the external bus during A/D conversion. If access occurs during A/D conversion, values might not fall within the indicated ranges.
Note 1. The conversion time is the sum of the sampling and the comparison times. The number of sampling states is indicated for the test conditions.
Note 2. Values in parentheses indicate the sampling time.

Table 2.42 A/D internal reference voltage characteristics

Item	Min	Typ	Max	Unit	Test conditions
A/D internal reference voltage	1.20	1.25	1.30	V	-

2.9 POR and LVD Characteristics

Table 2.46 Power-on reset circuit and voltage detection circuit characteristics

Item			Symbol	Min	Typ	Max	Unit	Test conditions
Voltage detection level	Power-on reset (POR)	Module-stop function disabled*1	V_{POR}	2.5	2.6	2.7	V	Figure 2.89
		Module-stop function enabled*2		2.0	2.35	2.7		
	Voltage detection circuit (LVD0)		V_{det0_1}	2.84	2.94	3.04		Figure 2.90
			V_{det0_2}	2.77	2.87	2.97		
			V_{det0_3}	2.70	2.80	2.90		
	Voltage detection circuit (LVD1)		V_{det1_1}	2.89	2.99	3.09		Figure 2.91
			V_{det1_2}	2.82	2.92	3.02		
			V_{det1_3}	2.75	2.85	2.95		
	Voltage detection circuit (LVD2)		V_{det2_1}	2.89	2.99	3.09		Figure 2.92
			V_{det2_2}	2.82	2.92	3.02		
			V_{det2_3}	2.75	2.85	2.95		
Internal reset time	Power-on reset time		t_{POR}	-	4.6	-	ms	Figure 2.89
	LVD0 reset time		t_{LVD0}	-	0.70	-		Figure 2.90
	LVD1 reset time		t_{LVD1}	-	0.57	-		Figure 2.91
	LVD2 reset time		t_{LVD2}	-	0.57	-		Figure 2.92
Minimum VCC down time			t_{VOFF}	200	-	-	µs	Figure 2.89, Figure 2.90
Response delay			t_{det}	-	-	200	µs	Figure 2.89 to Figure 2.92
LVD operation stabilization time (after LVD is enabled)			$T_{d(E-A)}$	-	-	10	µs	Figure 2.91, Figure 2.92
Hysteresis width (LVD1 and LVD2)			V_{LVH}	-	80	-	mV	

Note 1. The minimum VCC down time indicates the time when VCC is below the minimum value of voltage detection levels V_{POR}, V_{det1}, and V_{det2} for POR and LVD.
Note 2. The low-power function is disabled and DEEPCUT[1:0] = 00b or 01b.
Note 3. The low-power function is enabled and DEEPCUT[1:0] = 11b.

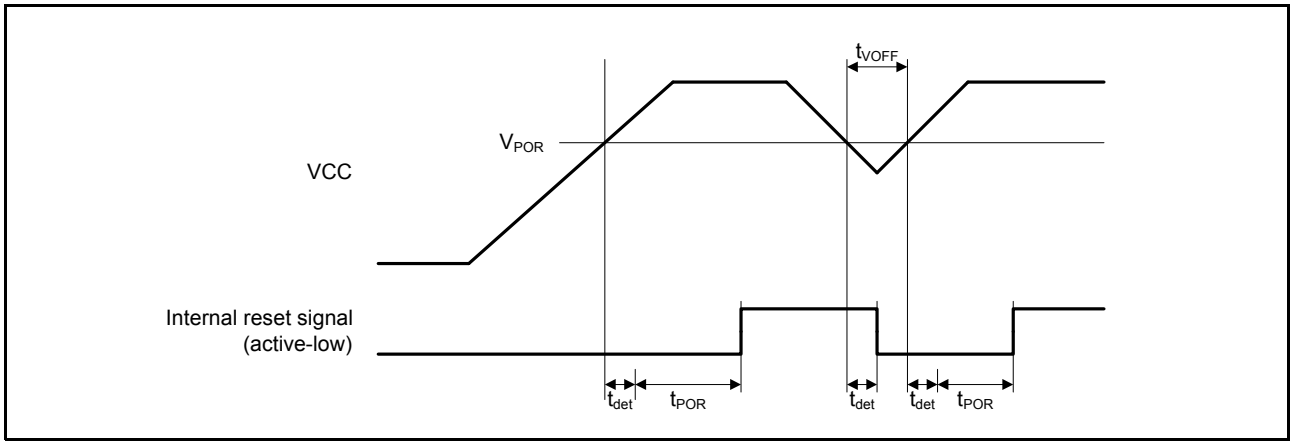


Figure 2.89 Power-on reset timing

Table 2.53 Data flash memory characteristics (2/2)
Conditions: Program or erase: FCLK = 4 to 60 MHz
Read: FCLK ≤ 60 MHz

Item	Symbol	FCLK = 4 MHz			20 MHz ≤ FCLK ≤ 60 MHz			Unit
		Min	Typ	Max	Min	Typ	Max	
Forced stop command	t_{FD}	-	-	32	-	-	20	µs
Data hold time*3	t_{DDRP}	20	-	-	20	-	-	Year

Note 1. The reprogram/erase cycle is the number of erasures for each block. When the reprogram/erase cycle is n times (n = 125,000), erasing can be performed n times for each block. For example, when 4-byte programming is performed 16 times for different addresses in 64-byte blocks, and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address several times as one erasure is not enabled. (Overwriting is prohibited.)
Note 2. This is the minimum number of times to guarantee all the characteristics after reprogramming. The guaranteed range is from 1 to the minimum value.
Note 3. This indicates the characteristics when reprogramming is performed within the specified range, including the minimum value.

2.15 Boundary Scan

Table 2.54 Boundary scan characteristics

Item	Symbol	Min	Typ	Max	Unit	Test conditions
TCK clock cycle time	t_{TCKcyc}	100	-	-	ns	Figure 2.95
TCK clock high pulse width	t_{TCKH}	45	-	-	ns	
TCK clock low pulse width	t_{TCKL}	45	-	-	ns	
TCK clock rise time	t_{TCKr}	-	-	5	ns	
TCK clock fall time	t_{TCKf}	-	-	5	ns	
TMS setup time	t_{TMSS}	20	-	-	ns	Figure 2.96
TMS hold time	t_{TMSH}	20	-	-	ns	
TDI setup time	t_{TDIS}	20	-	-	ns	
TDI hold time	t_{TDIH}	20	-	-	ns	
TDO data delay	t_{TDOD}	-	-	40	ns	
Boundary scan circuit startup time*1	T_{BSSTUP}	t_{RESWP}	-	-	-	Figure 2.97

Note 1. Boundary scan does not function until the power-on reset becomes negative.

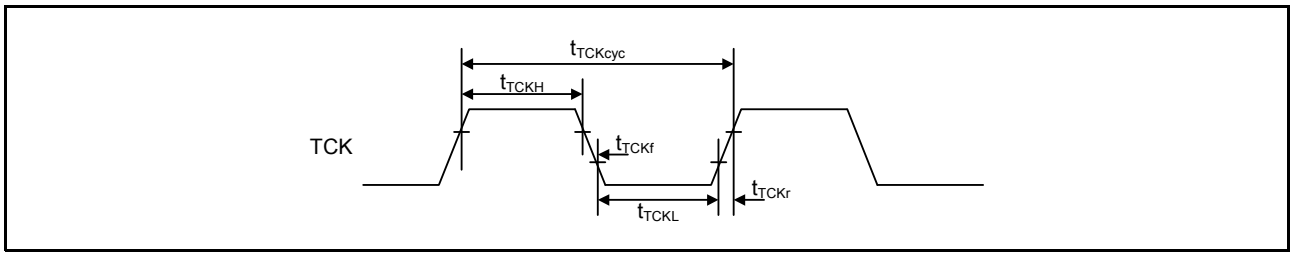


Figure 2.95 Boundary scan TCK timing

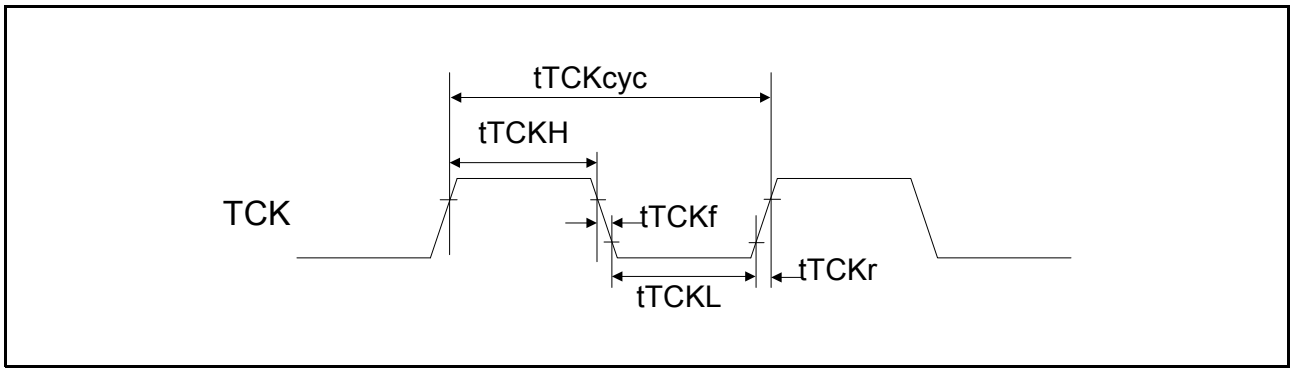


Figure 2.98 JTAG TCK timing

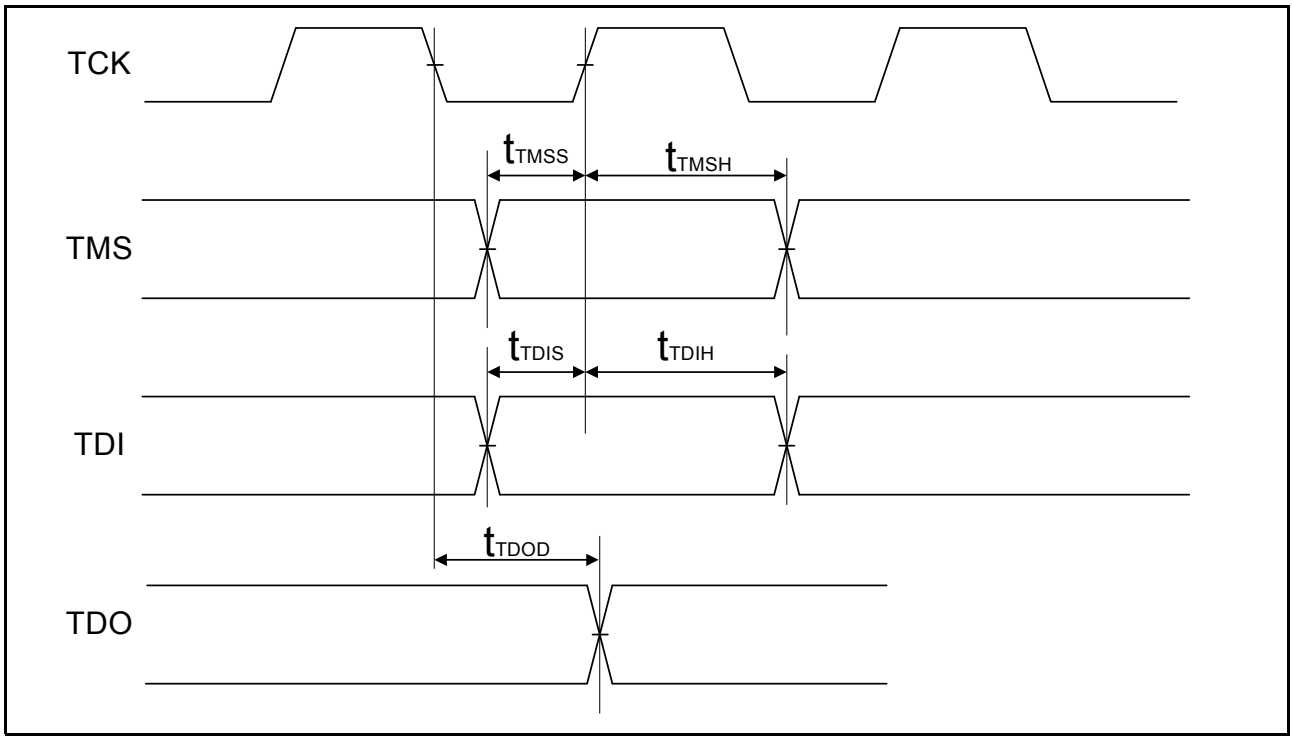


Figure 2.99 JTAG input/output timing

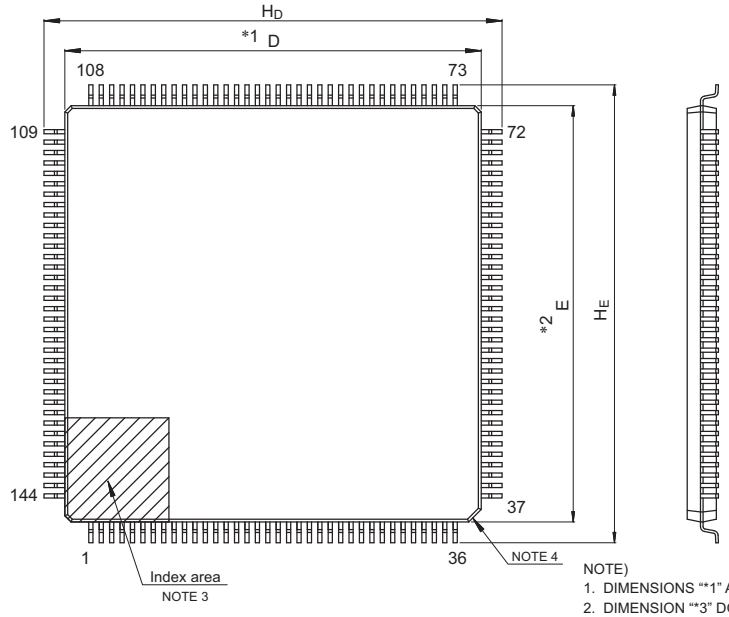
2.17 Serial Wire Debug (SWD)

Table 2.56 SWD

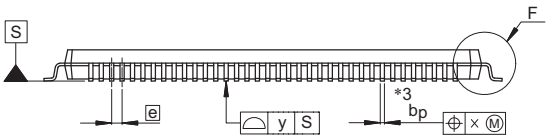
Item	Symbol	Min	Typ	Max	Unit	Test conditions
SWCLK clock cycle time	$t_{SWCKcyc}$	40	-	-	ns	Figure 2.100
SWCLK clock high pulse width	t_{SWCKH}	15	-	-	ns	
SWCLK clock low pulse width	t_{SWCKL}	15	-	-	ns	
SWCLK clock rise time	t_{SWCKr}	-	-	5	ns	
SWCLK clock fall time	t_{SWCKf}	-	-	5	ns	
SWDIO setup time	t_{SWDS}	8	-	-	ns	Figure 2.101
SWDIO hold time	t_{SWDH}	8	-	-	ns	
SWDIO data delay time	t_{SWDD}	2	-	28	ns	

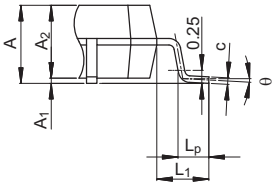
JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
P-LFQFP144-20x20-0.50	PLQP0144KA-B	—	1.2

Unit: mm



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.
3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA.
4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.





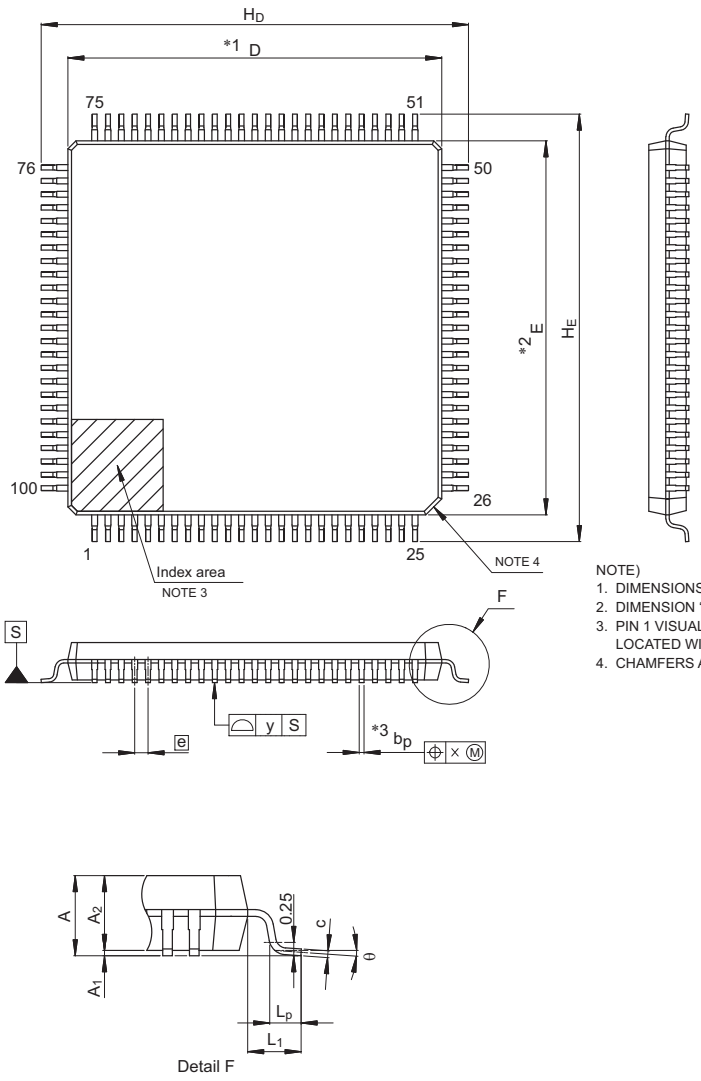
Detail F

Reference Symbol	Dimensions in millimeters		
	Min	Nom	Max
D	19.9	20.0	20.1
E	19.9	20.0	20.1
A_2	—	1.4	—
H_D	21.8	22.0	22.2
H_E	21.8	22.0	22.2
A	—	—	1.7
A_1	0.05	—	0.15
b_p	0.17	0.20	0.27
c	0.09	—	0.20
θ	0°	3.5°	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.08
L_p	0.45	0.6	0.75
L_1	—	1.0	—

Figure 1.5 144-pin LQFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
P-LFQFP100-14x14-0.50	PLQP0100KB-B	—	0.6

Unit: mm



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.
3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA.
4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

Reference Symbol	Dimensions in millimeters		
	Min	Nom	Max
D	13.9	14.0	14.1
E	13.9	14.0	14.1
A_2	—	1.4	—
H_D	15.8	16.0	16.2
H_E	15.8	16.0	16.2
A	—	—	1.7
A_1	0.05	—	0.15
b_p	0.15	0.20	0.27
c	0.09	—	0.20
θ	0°	3.5°	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.08
L_p	0.45	0.6	0.75
L_1	—	1.0	—

Figure 1.6 100-pin LQFP